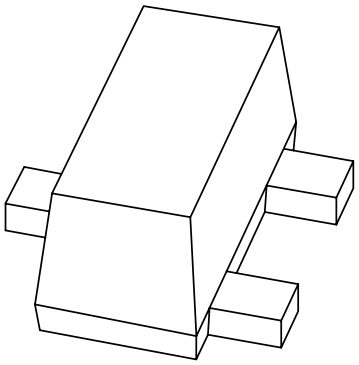
DATA SHEET



PDTA114YEF

PNP resistor-equipped transistor
R1 = 10 kΩ; R2 = 47 kΩ

Product specification

2002 Mar 15

Philips
Semiconductors

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PNP resistor-equipped transistor R1 = 10 kΩ; R2 = 47 kΩ

PDTA114YEF

FEATURES

- Built-in bias resistors
- 250 mW total power dissipation
- Very small 1.6 × 0.85 × 0.7 mm thin package
- Flat leads
- Excellent coplanarity
- Improved thermal behaviour
- Reduces number of components and required PCB area.

APPLICATIONS

- General purpose and switching amplification
- Inverter and interface circuits
- Driver circuits.

DESCRIPTION

PNP resistor-equipped transistor in a SOT490 (SC-89) plastic package.

MARKING

TYPE NUMBER	MARKING CODE
PDTA114YEF	37

QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	UNIT
V_{CEO}	collector-emitter voltage	–50	V
I_O	output current (DC)	–100	mA
R1	bias resistor	10	kΩ
R2	bias resistor	47	kΩ

PINNING

PIN	DESCRIPTION
1	base/input
2	emitter/ground (+)
3	collector/output

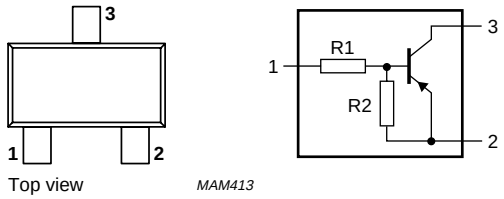


Fig.1 Simplified outline (SOT490) and symbol.

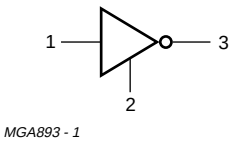


Fig.2 Equivalent inverter symbol.

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	–50	V
V_{CEO}	collector-emitter voltage	open base	–	–50	V
V_{EBO}	emitter-base voltage	open collector	–	–10	V
V_i	input voltage				
	positive		–	+6	V
	negative		–	–40	V
I_O	output current (DC)		–	–100	mA
I_{CM}	peak collector current		–	–100	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25$ °C; note 1	–	250	mW
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	150	°C
T_{amb}	operating ambient temperature		–65	+150	°C

Note

1. For mounting conditions, see *"Thermal considerations and footprint design for SOT490 in the SC18 Data Handbook"*.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j\text{-}a}$	thermal resistance from junction to ambient	in free air; note 1	500	K/W

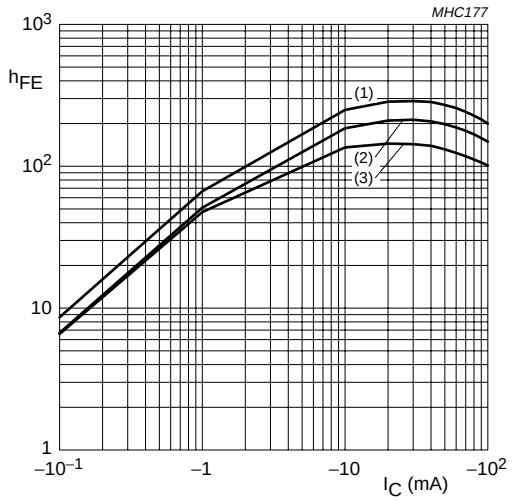
Note

1. For mounting conditions, see *"Thermal considerations and footprint design for SOT490 in the SC18 Data Handbook"*.

CHARACTERISTICS

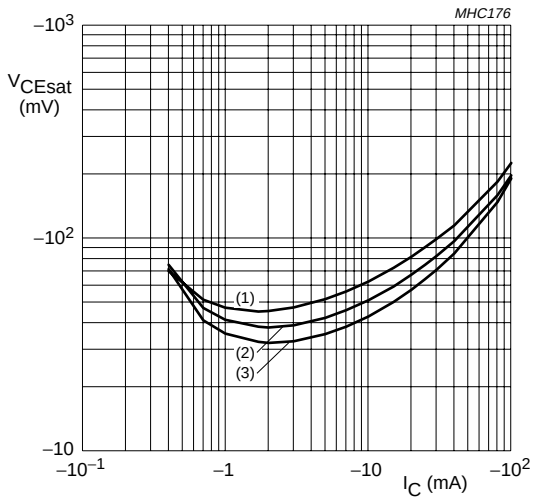
T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CBO}	collector-base cut-off current	V_{CB} = –50 V; I_E = 0	–	–	–100	nA
I_{CEO}	collector-emitter cut-off current	V_{CE} = –30 V; I_B = 0	–	–	–1	µA
		V_{CE} = –30 V; I_B = 0; T_j = 150 °C	–	–	–50	µA
I_{EBO}	emitter-base cut-off current	V_{EB} = –5 V; I_C = 0	–	–	–150	µA
h_{FE}	DC current gain	V_{CE} = –5 V; I_C = –5 mA	100	–	–	
V_{CEsat}	saturation voltage	I_C = –5 mA; I_B = –0.25 mA	–	–	–100	mV
$V_{i(off)}$	input off voltage	V_{CE} = –5 V; I_C = –100 µA	–	–	–0.5	V
$V_{i(on)}$	input on voltage	V_{CE} = –0.3 V; I_C = –1 mA	–1.4	–	–	V
R_1	input resistor		7	10	13	kΩ
$\frac{R2}{R1}$	resistor ratio		3.7	4.7	5.7	
C_c	collector capacitance	V_{CB} = –10 V; $I_E = i_e$ = 0; f = 1 MHz	–	–	3	pF



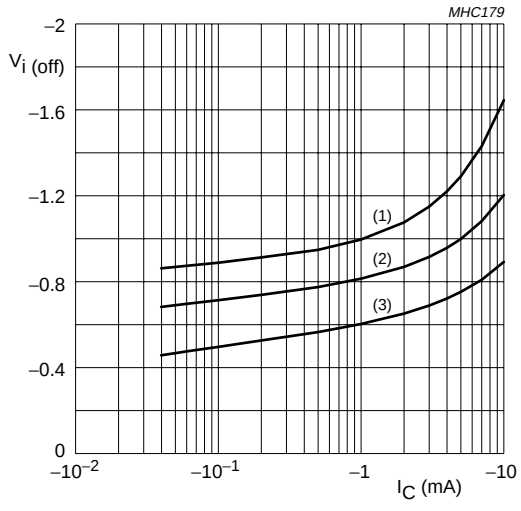
V_{CE} = −5 V.
(1) T_{amb} = 100 °C.
(2) T_{amb} = 25 °C.
(3) T_{amb} = −40 °C.

Fig.3 DC current gain as a function of collector current; typical values.



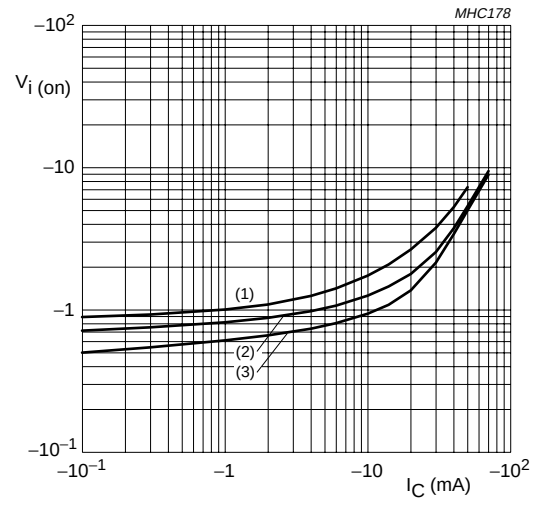
I_C/I_B = 20.
(1) T_{amb} = 100 °C.
(2) T_{amb} = 25 °C.
(3) T_{amb} = −40 °C.

Fig.4 Collector-emitter saturation voltage as a function of collector current; typical values.



V_{CE} = −5 V.
(1) T_{amb} = −40 °C.
(2) T_{amb} = 25 °C.
(3) T_{amb} = 100 °C.

Fig.5 Input-off voltage as a function of collector current; typical values.

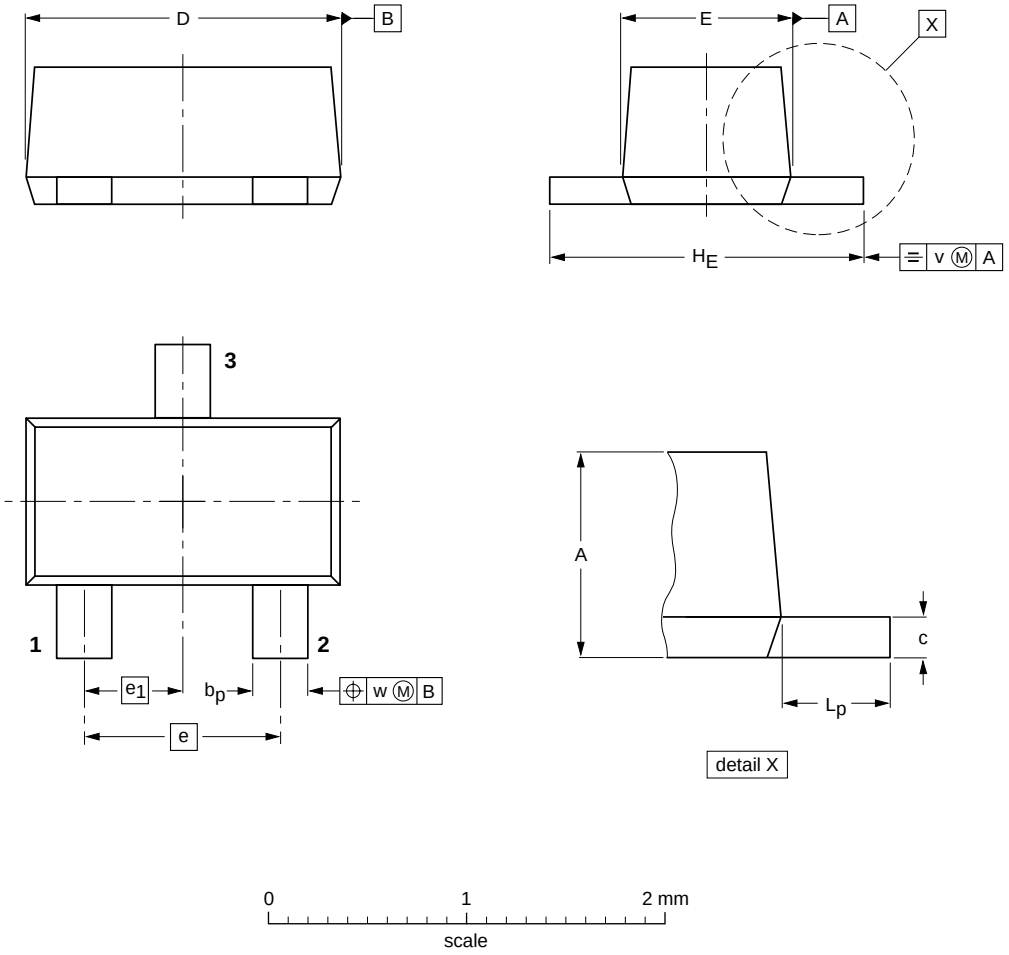


V_{CE} = −0.3 V.
(1) T_{amb} = −40 °C.
(2) T_{amb} = 25 °C.
(3) T_{amb} = 100 °C.

Fig.6 Input-on voltage as a function of collector current; typical values.

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads **SOT490**



DIMENSIONS (mm are the original dimensions)

UNIT	A	b_p	c	D	E	e	e_1	H_E	L_p	v	w
mm	0.8 0.6	0.33 0.23	0.2 0.1	1.7 1.5	0.95 0.75	1.0	0.5	1.7 1.5	0.5 0.3	0.1	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT490			SC-89			98-10-23

DATA SHEET STATUS

DATA SHEET STATUS[1]	PRODUCT STATUS[2]	DEFINITIONS
Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
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Printed in The Netherlands 613514/01/pp8 Date of release: 2002 Mar 15 Document order number: 9397 750 09366

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